BATOP optoelectronics

SAM™ Data Sheet SAM-1150-28-1ps-x, λ = 1150 nm

Laser wavelength	λ = 1150 nm
High reflection band	λ = 1080 .. 1190 nm
Absorbance	A_0 = 28 %
Modulation depth	ΔR = 16 %
Non-saturable loss	A_{ns} = 12 %
Saturation fluence	Φ_{sat} = 70 µJ/cm^2
Relaxation time constant	τ ~ 1 ps
Damage threshold	Φ_t = 900 µJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a copper heat sink with 12.7 mm ∅
x = 25.4 g	glued on a copper heat sink with with 25.4 mm ∅
x = 12.7 s	soldered on a copper heat sink with with 12.7 mm ∅
x = 25.4 s	soldered on a copper heat sink with with 25.4 mm ∅
x = 25.0 w	soldered on copper heat sink with with 25.0 mm ∅
x = FC	mounted on a 1 m single mode fiber cable with FC connector

Low intensity spectral reflectance